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RHRG3060_F085_30A, 600V Hyperfast Rectifier

July 2014



Features

- High Speed Switching (trr=45ns(Typ.) @ I_F=30A)
- Low Forward Voltage(V_F=1.64V(Typ.) @ I_F=30A)
- Avalanche Energy Rated
- AEC-Q101 Qualified

Applications

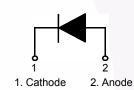
- Switching Power Supply
- Power Switching Circuits
- Automotive and General Purpose

Max Ratings (600V, 30A)

The RHRG3060_F085 is an Hyperfast[™] diode with soft recovery characteristics (trr < 45ns). It has half the recovery time of ultrafast diode and is of silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of automotive switching power supplies and other power switching automotive applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Pin Assignments





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{RRM}	Peak Repetitive Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current $@T_{C} = 25^{\circ}C$	30	А	
I _{FSM}	Non-repetitive Peak Surge Current (Halfwave 1 Phase 50Hz)	90	A	
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ	
T _{J,} T _{STG}	Operating Junction and Storage Temperature	- 55 to +175	°C	

Thermal Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Max	Units
$R_{ ext{ heta}JC}$	Maximum Thermal Resistance, Junction to Case	0.66	°C/W
$R_{ ext{ heta}JA}$	Maximum Thermal Resistance, Junction to Ambient	45	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Tube	Quantity
RHRG3060	RHRG3060_F085	TO-247	-	30

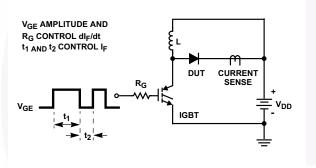
Symbol	Parameter Instantaneous Reverse Current	Conditions		Min.	Тур.	Max	Units
		V _R = 600V	T _C = 25 °C	-	-	250	uA
			T _C = 175 °C	-	-	1.5	mA
V _{FM} ¹	Instantaneous Forward Voltage	I _F = 30A	T _C = 25 °C T _C = 175 °C	-	1.64 1.24	2.1 1.7	V V
t _{rr} ² Reverse	Reverse Recovery Time	I _F =1A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	24	40	ns
		I_F =30A, di/dt = 200A/µs, V _{CC} = 390V	T _C = 25 °C T _C = 175 °C	-	33 136	45 -	ns ns
t _a t _b Q _{rr}	Reverse Recovery Time Reverse Recovery Charge	I _F =30A, di/dt = 200A/μs, V _{CC} = 390V	T _C = 25 °C	-	19 14 60	-	ns ns nC

Notes:

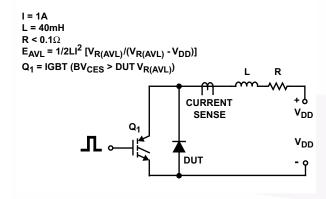
- 1. Pulse : Test Pulse width = 300μ s, Duty Cycle = 2%
- 2. Guaranteed by design

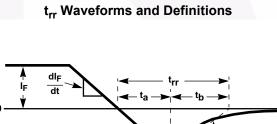
Test Circuit and Waveforms





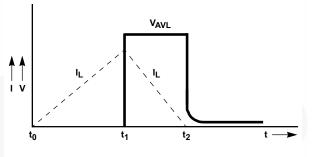


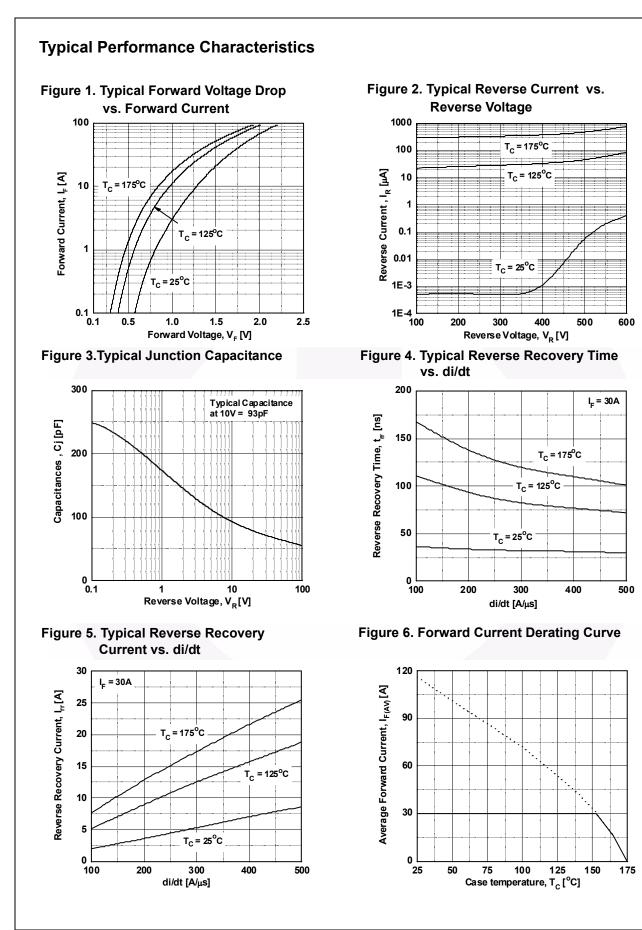


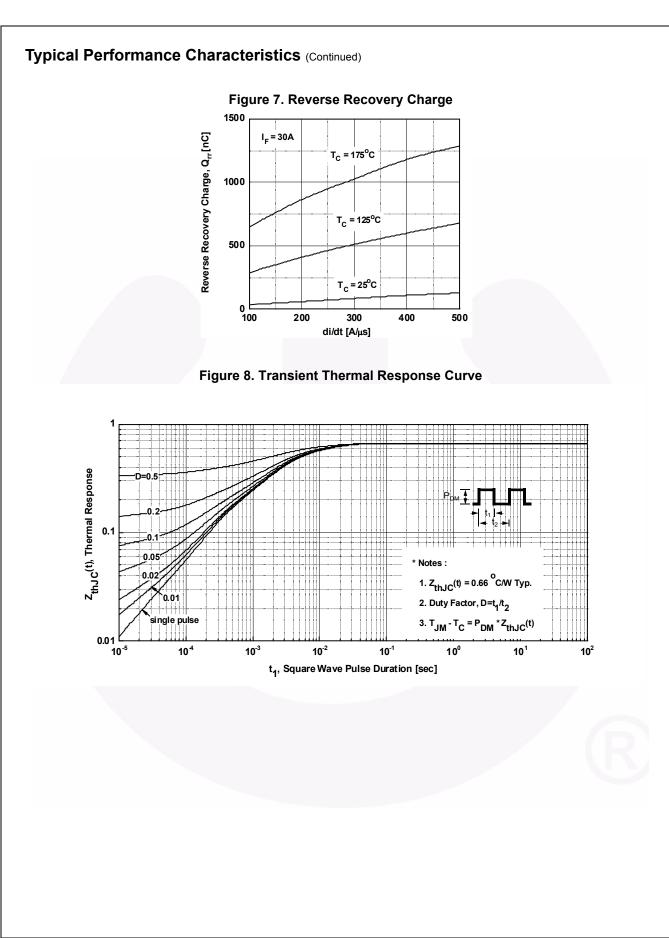


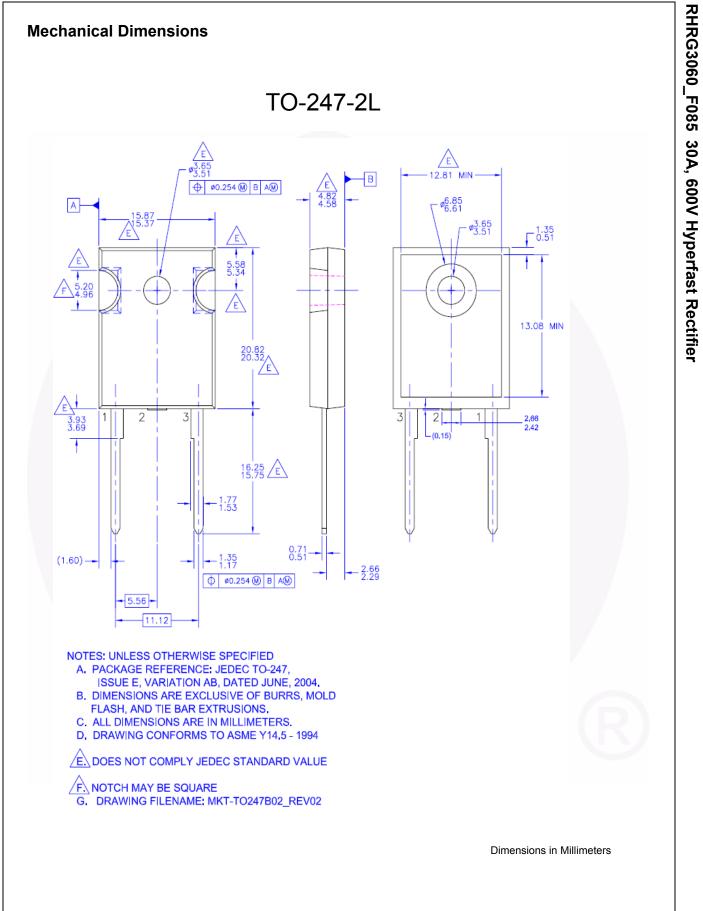


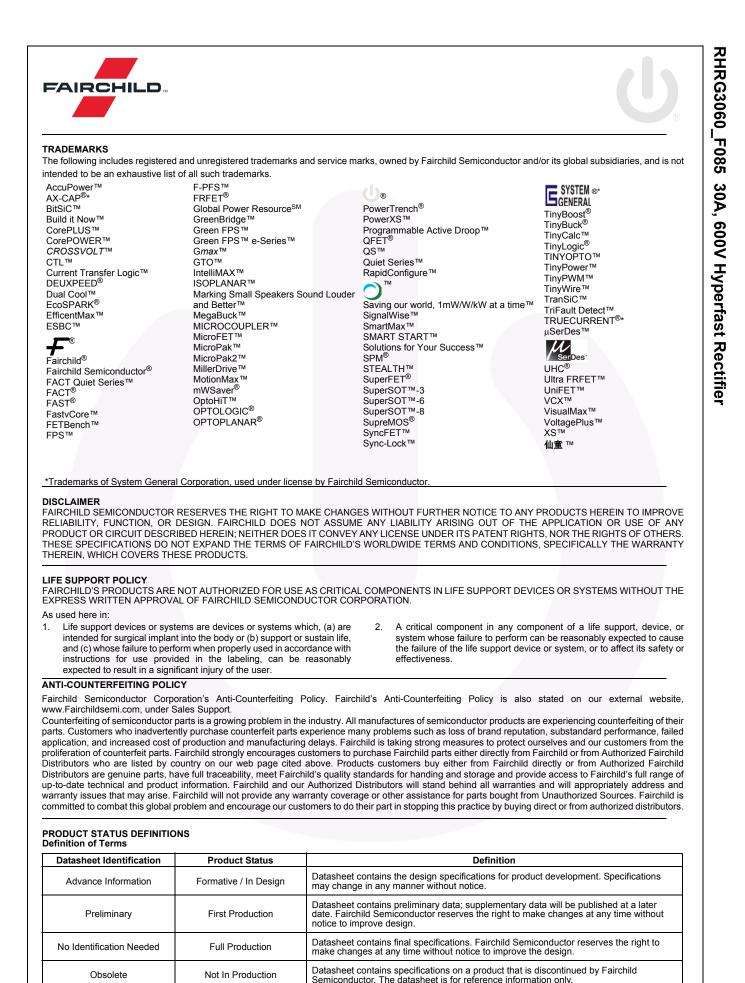
Avalanche Current and Voltage Waveforms











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